TECHNICAL DATA
DATA SHEET 721, REV -

HERMETIC POWER MOSFET P-CHANNEL

FEATURES:

- **-100 Volt, 0.22 Ohm MOSFET**
- **Isolated and Hermetically Sealed**
- **Simple Drive Requirements**

MAXIMUM RATINGS

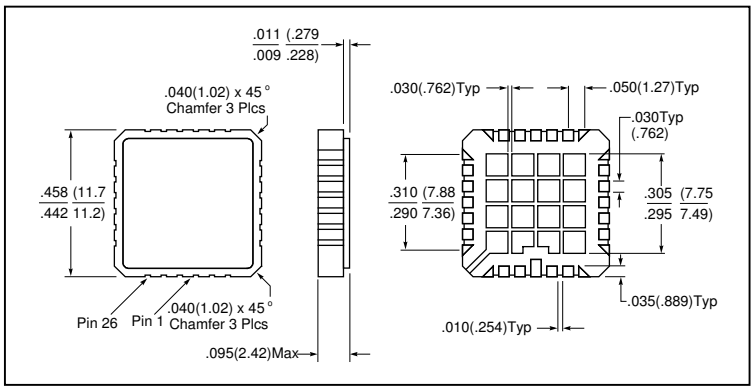
ALL RATINGS ARE AT T_A = 25°C UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MIN.	TYP.	MAX.	UNITS
GATE TO SOURCE VOLTAGE	V_{GS}	-	-	±20	Volts
CONTINUOUS DRAIN CURRENT V_{GS}=10V, T_C = 25°C V_{GS}=10V, T_C = 100°C	I_D	-	-	-14 -9.5	Amps
OPERATING AND STORAGE TEMPERATURE	T_{OP}/T_{STG}	-55	-	150	°C
TERMAL RESISTANCE JUNCTION TO CASE	$R_{\theta JC}$	-	-	1.36	°C/W
TOTAL DEVICE DISSIPATION @ T_C = 25°C	P_D	-	-	90	Watts

ELECTRICAL CHARACTERISTICS

DRAIN TO SOURCE BREAKDOWN VOLTAGE V_{GS} = 0V, I_D = 1.0mA	BV_{DSS}	-100	-	-	Volts
DRAIN TO SOURCE ON STATE RESISTANCE V_{GS} = -10V, I_D = -9.5A V_{GS} = -10V, I_D = -14A	$R_{DS(ON)}$	-	-	 0.22 0.24	Ω
GATE THRESHOLD VOLTAGE V_{DS} = V_{GS}, I_D = -250µA	$V_{GS(th)}$	-2.0	-	-4.0	Volts
FORWARD TRANSCONDUCTANCE V_{DS} ≥ -15V, I_{DS} = -9.5A	g_{fs}	6.2	-	-	S(1/Ω)
ZERO GATE VOLTAGE DRAIN CURRENT V_{DS} = 0.8xMax. Rating, V_{GS} = 0V V_{DS} = 0.8xMax. Rating V_{GS} = 0V, T_J = 125°C	I_{DSS}	-	-	 -25 -250	µA
GATE TO SOURCE LEAKAGE FORWARD @ RATED GATE TO SOURCE LEAKAGE REVERSE V_{GS}	I_{GSS}	-	-	100 -100	nA
TOTAL GATE CHARGE V_{GS} = -10 V, GATE TO SOURCE CHARGE V_{DS} = .5X max. rating, GATE TO DRAIN CHARGE I_D = .5 x rated I_D	Q_g Q_{gs} Q_{gd}	31 3.7 7.0	-	60 13 35.2	nC
TURN ON DELAY TIME V_{DD} = -50V RISE TIME I_D = 14A TURN OFF DELAY TIME R_G = 9.1Ω FALL TIME	$t_{d(ON)}$ t_r $t_{d(ON)}$ t_f	-	-	35 85 85 65	nsec
DIODE FORWARD VOLTAGE T_J = 25°C, I_S = 14A, V_{GS} = 0V	V_{SD}	-	-	-4.2	Volts
DIODE REVERSE RECOVERY TIME T_J = 25°C REVERSE RECOVERY CHARGE I_f = 14A di/dt = -100A/sec	t_{rr} Q_{rr}	-	-	280 3.6	nsec µC
INPUT CAPACITANCE V_{GS} = 0 Volts OUTPUT CAPACITANCE V_{DS} = 25 Volts REVERSE TRANSFER CAPACITANCE f = 1 MHz	C_{iss} C_{oss} C_{rss}	-	1400 600 200	-	pF

MECHANICAL DIMENSIONS: in Inches / m



LCC-28T

PINOUT TABLE

	PINS(S) 1 & 15-28	PINS 5-11	PINS 2, 3, 13, & 14
MOSFET - LCC-28T	SOURCE	DRAIN	GATE

TECHNICAL DATA

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